NSN 5962-01-171-9685

Memory Microcircuit - Page 1 of 1



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Storage Tempurature Range:
-65.0/+150.0 degrees celsius
Features Provided:
Bipolar and programmable and hermetically sealed and high impedance and low level
Inclosure Material:
Ceramic
Inclosure Configuration:
Dual-in-line
Output Logic Form:
Transistor-transistor logic
Input Circuit Pattern:
6 input
Case Outline Source And Designator:
D-3 mil-m-38510
Terminal Surface Treatment:
Solder
Voltage Rating And Type Per Characteristic:
5.5 volts power source
Memory Device Type:
Rom
Test Data Document:
81349-mil-m-38510 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification
format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain
environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).
Terminal Type And Quantity:
24 printed circuit
Shelf Life:
N/a
Unit Of Measure:

Demilitarization:
Yes - demil/mli
Fiig:
A458a0